

Absolute Maximum Ratings (Ta = 25° C)

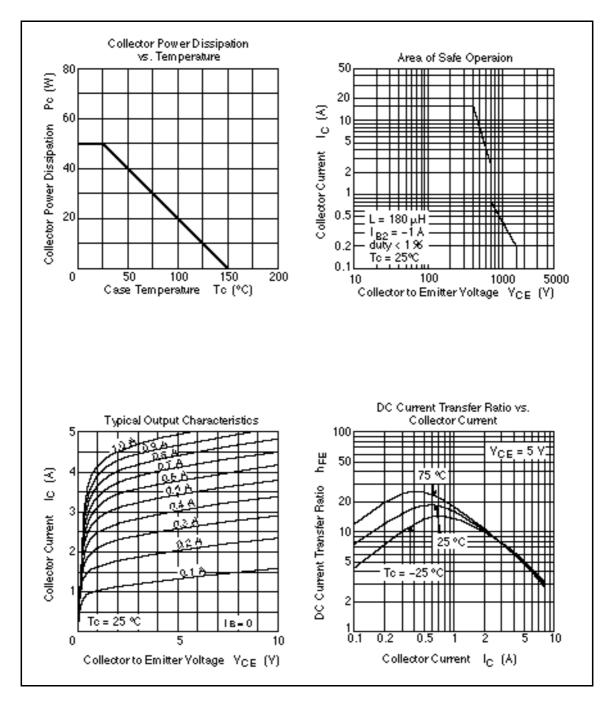
Item	Symbol	Ratings	Unit
Collector to emitter voltage	V _{ces}	1500	V
Emitter to base voltage	V _{EBO}	6	V
Collector current	I _c	8	А
Collector peak current	İ _{c(peak)}	16	А
Collector power dissipation	P _c ^{Note1}	50	W
Junction temperature	Тј	150	°C
Storage temperature	Tstg	–55 to +150	°C
Collector to emitter diode forward current	I _D	8	А

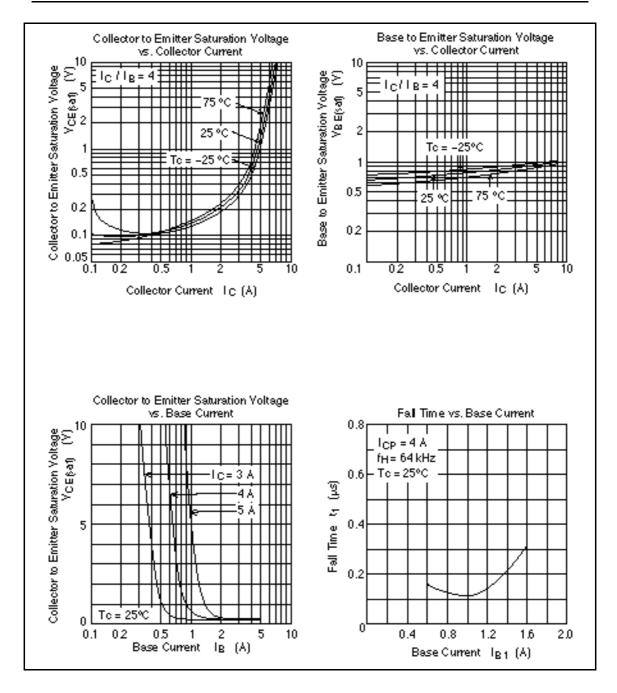
Note: 1. Value at $Tc = 25^{\circ}C$

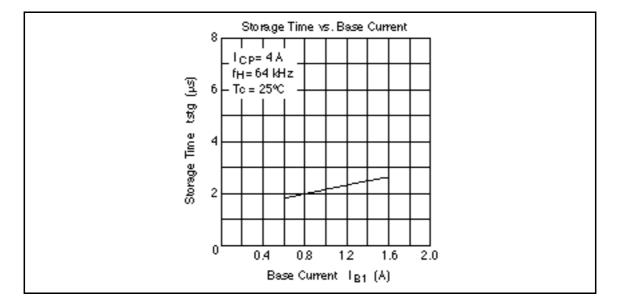
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Emitter to base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	6	—		V	$I_{\rm E} = 400 {\rm mA}, \ I_{\rm C} = 0$
Collector cutoff current	I _{CES}			500	μA	$V_{ce} = 1500V, R_{be} = 0$
DC current transfer ratio	h_{FE1}	5		25		$V_{ce} = 5 V, I_c = 1A$
DC current transfer ratio	h_{FE2}	4	_	6		$V_{ce} = 5 V, I_{c} = 5A$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	5	V	$I_{\rm C} = 5A, I_{\rm B} = 1.25A$
Base to emitter saturation voltage	$V_{\text{BE(sat)}}$	_		1.5	V	$I_{\rm C} = 5A, I_{\rm B} = 1.25A$
Collector to emitter diode forward voltage	V_{ECF}	_	_	2	V	I _F = 8A
Fall time	t _f	_	0.2	0.4	μs	$I_{CP} = 4A, I_{B1} = 1.2A$ $f_{H} = 31.5 \text{kHz}$
Fall time	t _f	_	0.15	_	μs	$I_{CP} = 4A, I_{B1} = 1A$ $f_{H} = 64kHz$

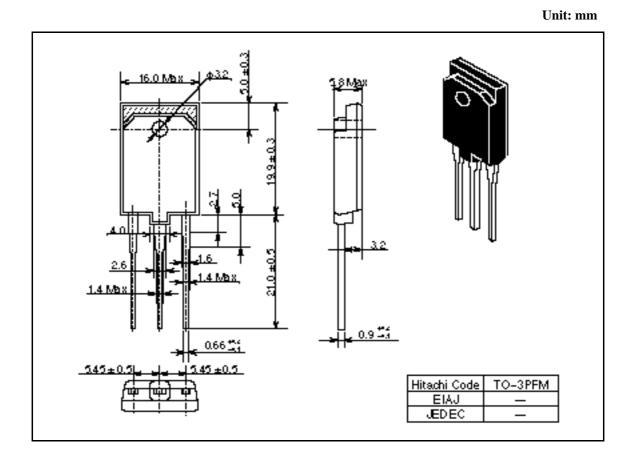
Main Characteristics







Package Dimensions



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